NPN Epitaxial Planar Silicon Transistor

2SC3495



High hFE, Low-Frequency General-Purpose Amplifier Applications

Applications

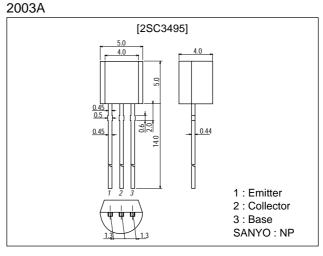
· AF amplifier, various driver, muting circuit.

Features

- · Adoption of FBET process.
- · High DC current gain (h_{FE} =500 to 2000).
- · High breakdown voltage ($V_{CEO} \ge 100V$).
- · Low collector-to-emitter saturation voltage $(V_{CE(sat)} \le 0.5V)$.
- High V_{EBO} ($V_{EBO} \ge 15V$).
- \cdot Small C_{ob} (C_{ob}=1.8pF typ).

Package Dimensions

unit:mm



Specifications

Absolute Maximum Ratings at $Ta = 25^{\circ}C$

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V _{CBO}		120	V
Collector-to-Emitter Voltage	VCEO		100	V
Emitter-to-Base Voltage	VEBO		15	V
Collector Current	IC		50	mA
Collector Current (Pulse)	ICP		100	mA
Base Current	Ι _Β		10	mA
Collector Dissipation	PC		500	mW
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Electrical Characteristics at $Ta = 25^{\circ}C$

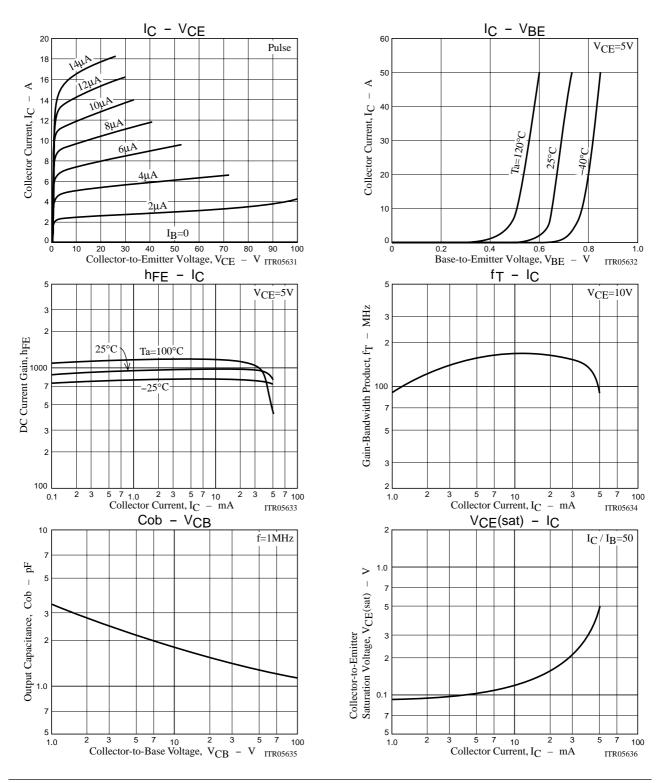
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Onit
Collector Cutoff Current	ICBO	V _{CB} =80V, I _E =0			0.1	μA
Emitter Cutoff Current	IEBO	V _{EB} =10V, I _C =0			0.1	μA
DC Current Gain	h _{FE}	V _{CE} =5V, I _C =10mA	500	1000	2000	
Gain-Bandwidth Product	fT	V _{CE} =10V, I _C =10mA		170		MHz
Output Capacitance	Cob	V _{CB} =10V, f=1MHz		1.8		pF

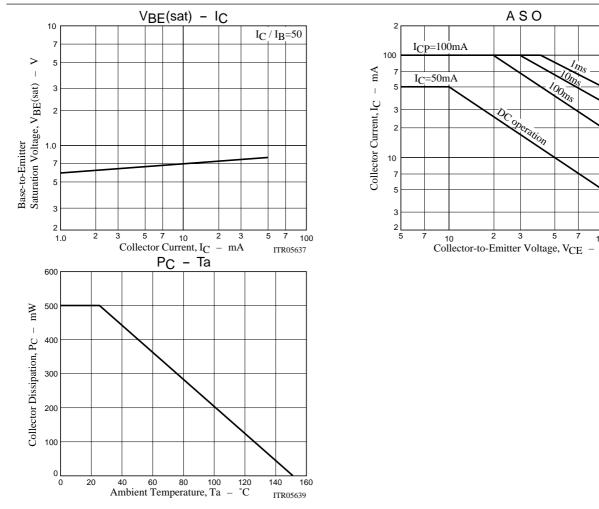
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Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Unit
Collector-to-Emitter Saturation Voltage	V _{CE(sat)}	I _C =10mA, I _B =200μA		0.1	0.5	V
Base-to-Emitter Saturation Voltage	V _{BE(sat)}	I _C =10mA, I _E =200µA		0.7	1.0	V
Collector-to-Base Breakdown Voltage	V _(BR) CBO	I _C =10μA, I _E =0	120			V
Collector-to-Emitter Breakdown Voltage	V(BR)CEO	I _C =1mA, R _{BE} =∞	100			V
Emitter-to-Base Breakdown Voltage	V(BR)EBO	I _E =10μΑ, I _C =0	15			V





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